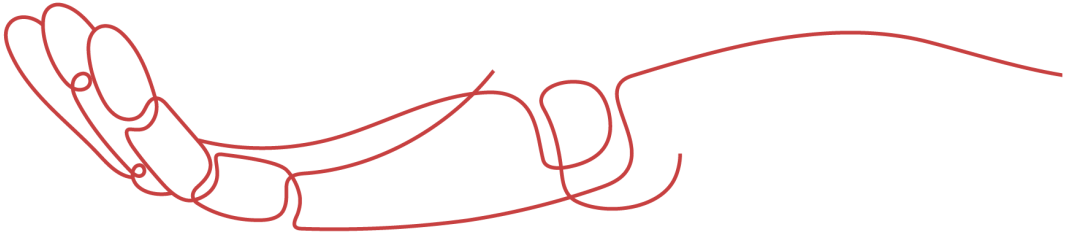




PRODUCT DATA SHEET



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Datasheet



Resources

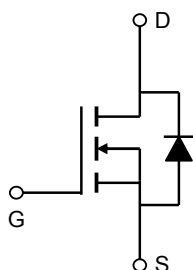


Samples

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO_questions@jgsemi.com.

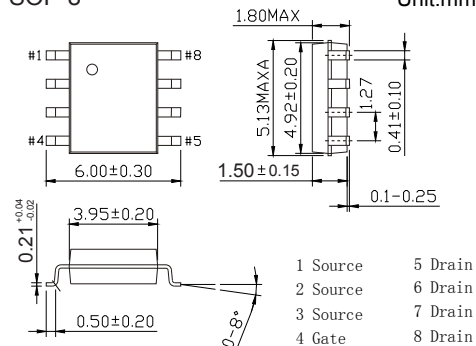
■ Features

- $V_{DS} (V) = 30V$
- $I_D = 18 A$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 5.5m\Omega$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 7.5m\Omega$ ($V_{GS} = 4.5V$)



SOP-8

Unit:mm



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current	$T_A=25^\circ C$	I_D	18	A
	$T_A=70^\circ C$		14	
Pulsed Drain Current		I_{DM}	140	
Avalanche Current		I_{AR}	42	
Repetitive Avalanche Energy	$L=0.1mH$	E_{AR}	88	mJ
Power Dissipation	$T_A=25^\circ C$	P_D	3.1	W
	$T_A=70^\circ C$		2	
Thermal Resistance.Junction- to-Ambient	$t \leq 10s$	R_{thJA}	40	$^\circ C/W$
	Steady-State		75	
Thermal Resistance.Junction- to-Lead		R_{thJL}	24	$^\circ C$
Junction Temperature		T_J	150	
Storage Temperature Range		T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{DSS}	I _D =250 μ A, V _{GS} =0V	30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V			1	μ A
		V _{DS} =30V, V _{GS} =0V, T _J =55°C			5	
Gate-Body Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} = $\pm$ 20V			$\pm$ 100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250 μ A	1.3		2.5	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =18A			5.5	m Ω
		V _{GS} =10V, I _D =18A, T _J =125°C			8	
		V _{GS} =4.5V, I _D =16A			7.5	
On State Drain Current	I _{D(on)}	V _{GS} =10V, V _{DS} =5V	140			A
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =18A		53		S
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =15V, f=1MHz		1910	2300	pF
Output Capacitance	C _{oss}			316		
Reverse Transfer Capacitance	C _{rss}			227		
Gate Resistance	R _g	V _{GS} =0V, V _{DS} =0V, f=1MHz	0.7		2.1	Ω
Total Gate Charge (10V)	Q _g	V _{GS} =10V, V _{DS} =15V, I _D =18A		37	44.5	nC
Total Gate Charge (4.5V)				18		
Gate Source Charge	Q _{gs}			4.8		
Gate Drain Charge	Q _{gd}			11		
Turn-On DelayTime	t _{d(on)}	V _{GS} =10V, V _{DS} =15V, R _L =0.83 Ω , R _{GEN} =3 Ω		8.1		ns
Turn-On Rise Time	t _r			8.6		
Turn-Off DelayTime	t _{d(off)}			29		
Turn-Off Fall Time	t _f			8		
Body Diode Reverse Recovery Time	t _{rr}	I _F = 18A, di/dt= 500A/us		14	17	nC
Body Diode Reverse Recovery Charge	Q _{rr}			40		
Maximum Body-Diode Continuous Current	I _S				4	A
Diode Forward Voltage	V _{SD}	I _S =1A, V _{GS} =0V			1	V

Note : The static characteristics in Figures 1 to 6 are obtained using <300 μ s pulses, duty cycle 0.5% max.

■ Typical Characteristics

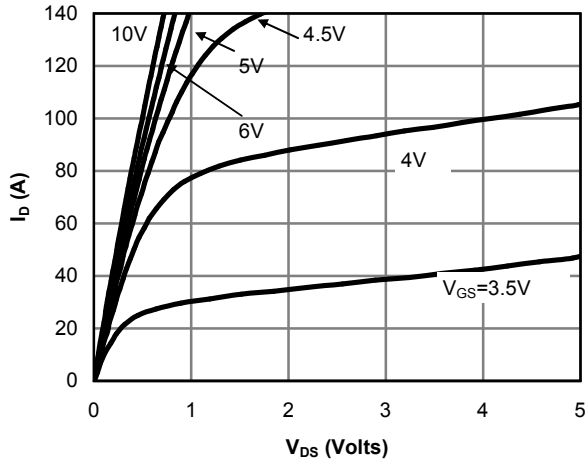


Fig 1: On-Region Characteristics (Note E)

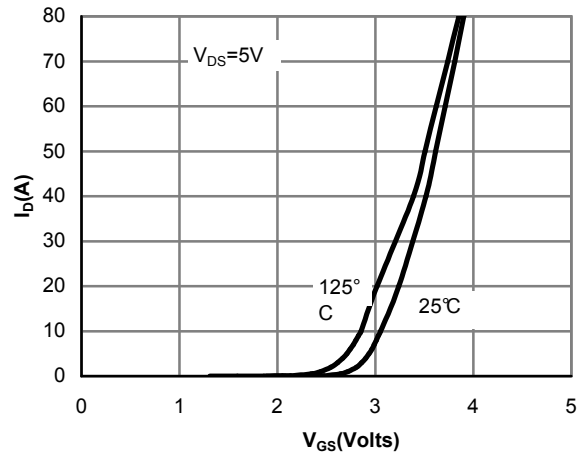


Figure 2: Transfer Characteristics (Note E)

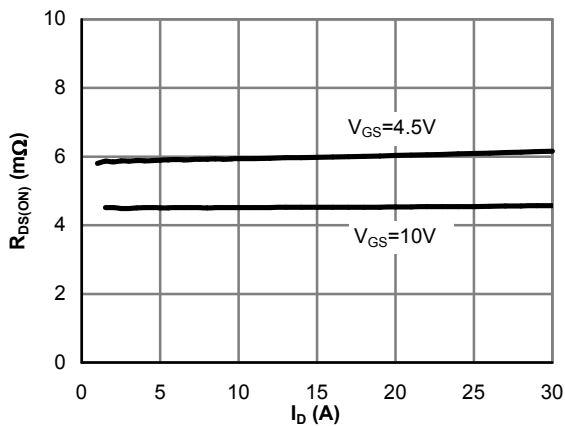


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

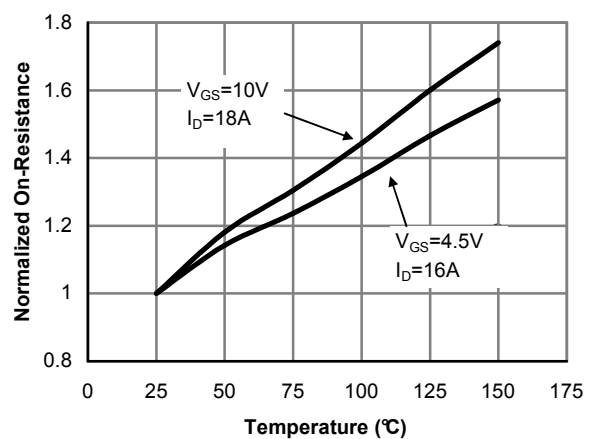


Figure 4: On-Resistance vs. Junction Temperature (Note E)

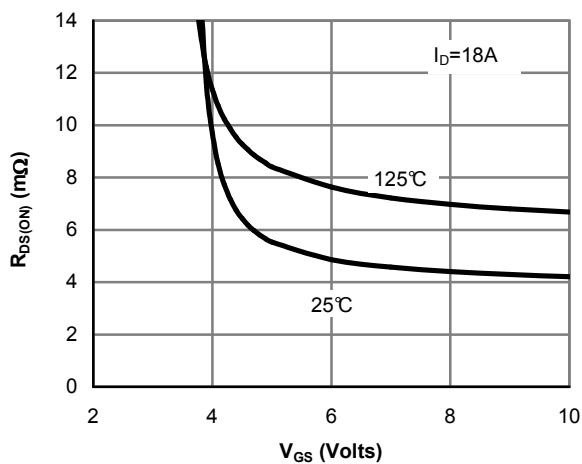


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

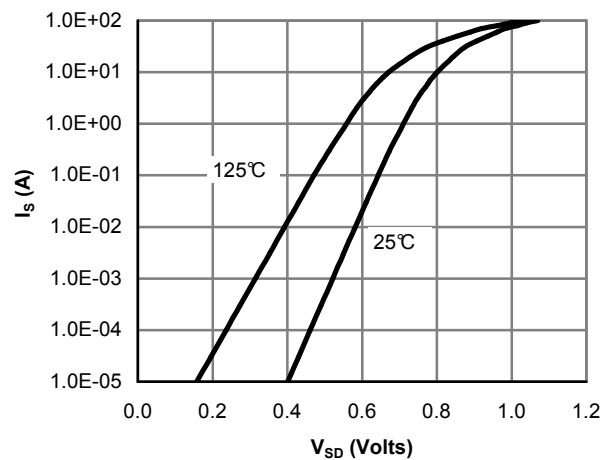
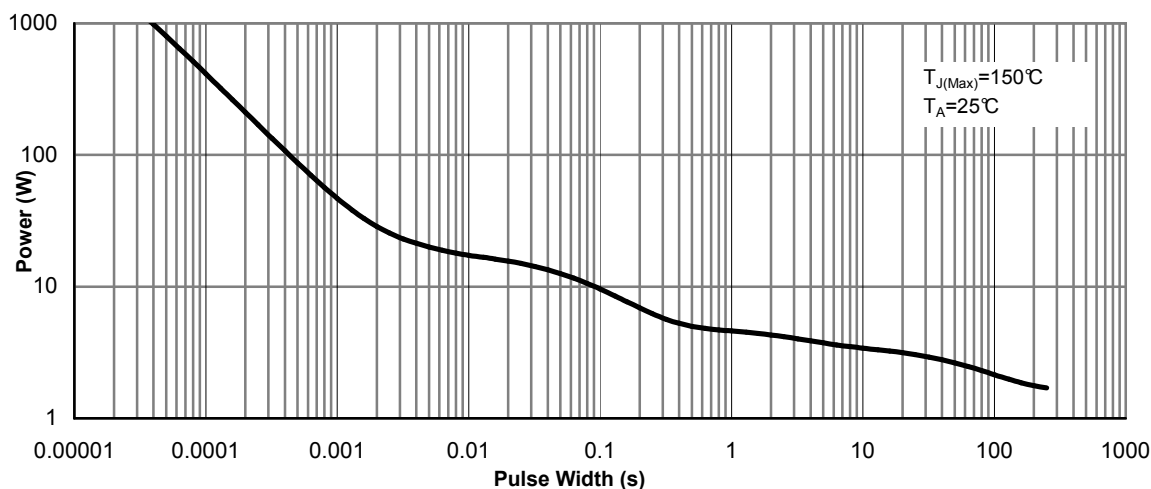
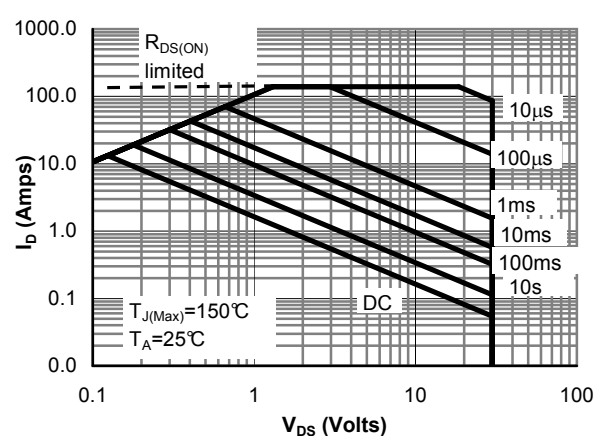
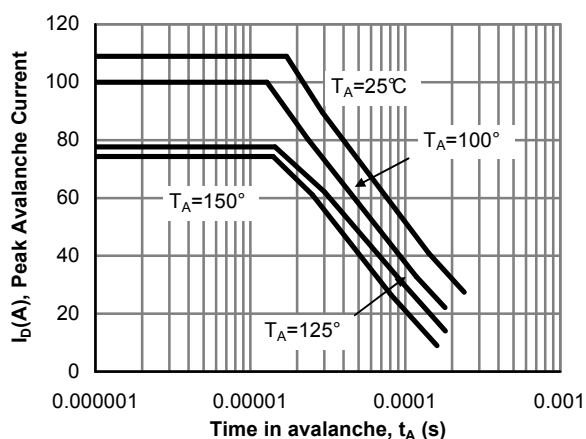
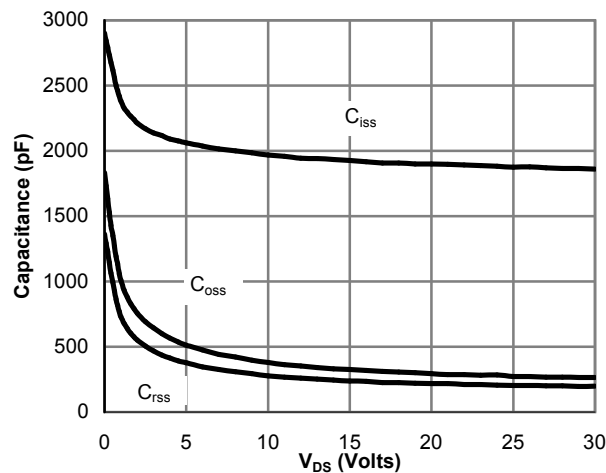
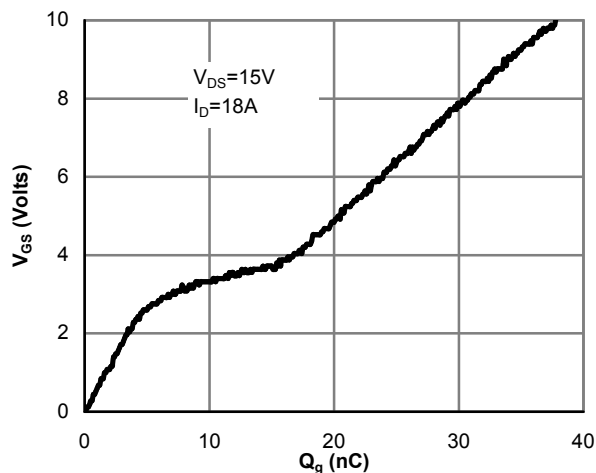
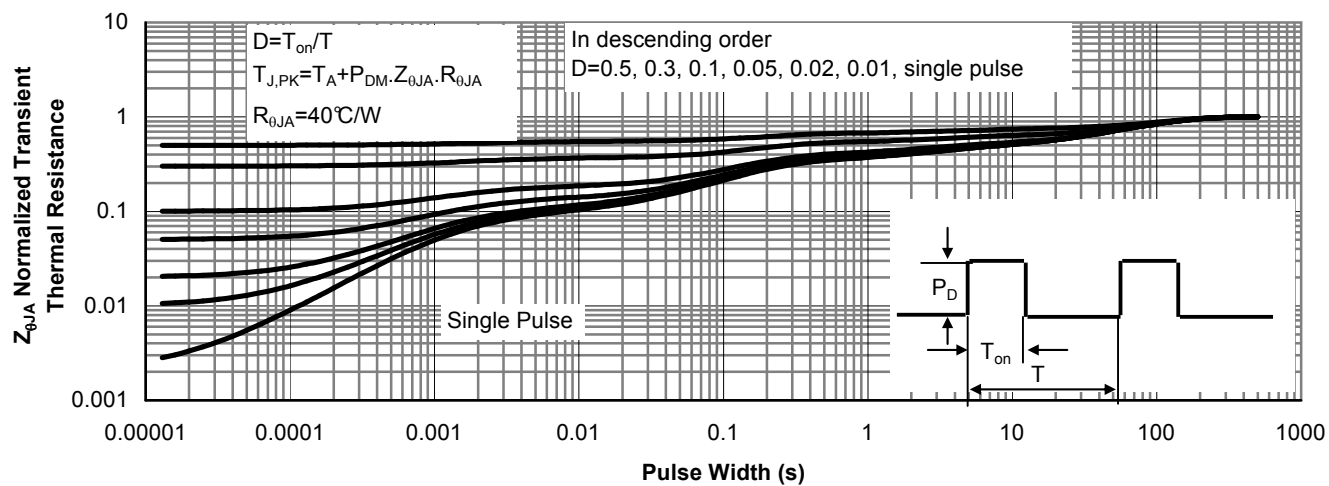


Figure 6: Body-Diode Characteristics (Note E)

■ Typical Characteristics



■ Typical Characteristics



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